



Silicon Nitride and Its Application

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Message from the Guest Editors

The properties of silicon nitride, such as its low propagation loss, high power handling, wide transparency window extended to the visible spectrum, and CMOS-compatibility make it an ideal platform for use in photonic integrated circuits (PICs) for certain applications such as LiDAR, sensing, bio-spectroscopy, communication, and of course quantum domain. There are different types of SiN technology, such as LPCVD and PECVD, each with distinct features and capabilities. This Special Issue aims to attract paper submissions on both technology development and from an application point of view.

Globally, state-of-the-art research is taking place, where novel and highly strategic domains are being targeted, from nonlinear photonics for special laser integration (e.g., dual-comb and mode lock), to extremely low loss waveguides for scalable quantum chips, high power handling chips for free-space communication, optical beam forming for 5G, and LiDAR will be considered in this Special Issue.

